

# NRVBB1060, NRVBB1060W1

## Switch-mode Power Rectifier

This switch-mode power rectifier uses the Schottky Barrier principle with a platinum barrier metal. This state-of-the-art device has the following features:

### Features

- Low Forward Voltage
- 175°C Operating Junction Temperature
- Low Power Loss/High Efficiency
- High Surge Capacity
- For Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device

### Applications

- Power Supply – Output Rectification
- Power Management

### Mechanical Characteristics

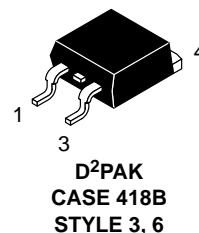
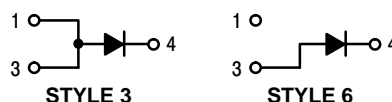
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.7 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



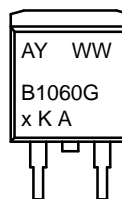
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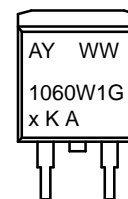
## SCHOTTKY BARRIER RECTIFIER 10 AMPERES, 60 VOLTS



### MARKING DIAGRAMS



**NRVBB1060**



**NRVBB1060W1**

- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package
- xKA = Diode Polarity
- x = N or A

### ORDERING INFORMATION

Device	Package	Shipping†
NRVBB1060T4G	D <sup>2</sup> PAK (Pb-Free)	800/Tape & Reel
NRVBB1060W1T4G	D <sup>2</sup> PAK (Pb-Free)	800/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NRVBB1060, NRVBB1060W1

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	60	V
Average Rectified Forward Current (Rated $V_R$ ) $T_C = 133^\circ\text{C}$	$I_{F(AV)}$	10	A
Peak Repetitive Forward Current (Rated $V_R$ , Square Wave, 20 kHz) $T_C = 133^\circ\text{C}$	$I_{FRM}$	20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	$I_{FSM}$	150	A
Peak Repetitive Reverse Surge Current (2.0 $\mu\text{s}$ , 1.0 kHz)	$I_{RRM}$	0.5	A
Operating Junction Temperature (Note 1)	$T_J$	-65 to +175	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-65 to +175	$^\circ\text{C}$
Voltage Rate of Change (Rated $V_R$ )	$dv/dt$	10,000	V/ $\mu\text{s}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

## THERMAL CHARACTERISTICS

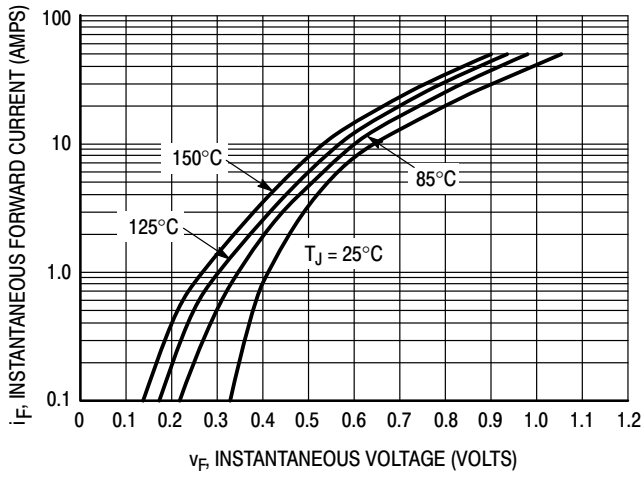
Maximum Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.0	$^\circ\text{C/W}$
Maximum Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	60	$^\circ\text{C/W}$

## ELECTRICAL CHARACTERISTICS

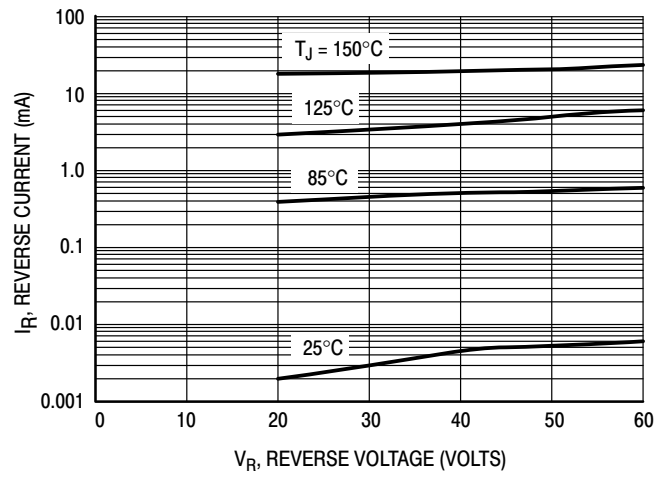
Maximum Instantaneous Forward Voltage (Note 2) ( $i_F = 10$ Amps, $T_C = 125^\circ\text{C}$ ) ( $i_F = 10$ Amps, $T_C = 25^\circ\text{C}$ ) ( $i_F = 20$ Amps, $T_C = 125^\circ\text{C}$ ) ( $i_F = 20$ Amps, $T_C = 25^\circ\text{C}$ )	$v_F$	0.7 0.8 0.85 0.95	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_C = 125^\circ\text{C}$ ) (Rated dc Voltage, $T_C = 25^\circ\text{C}$ )	$i_R$	25 0.10	mA

2. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

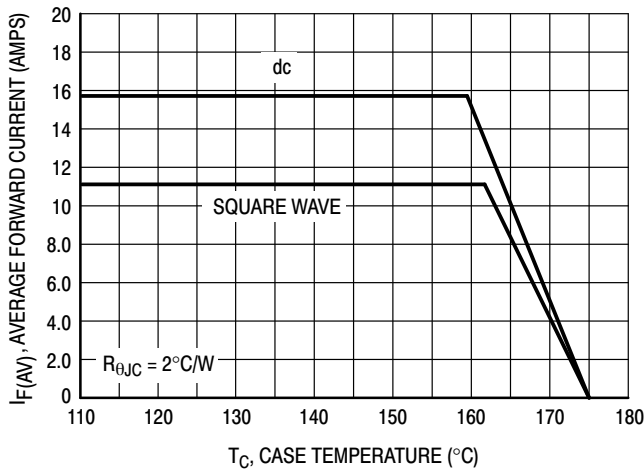
# NRVBB1060, NRVBB1060W1



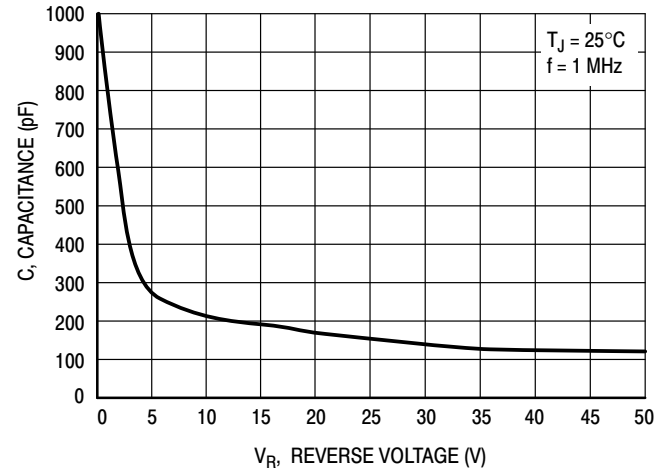
**Figure 1. Typical Forward Voltage**



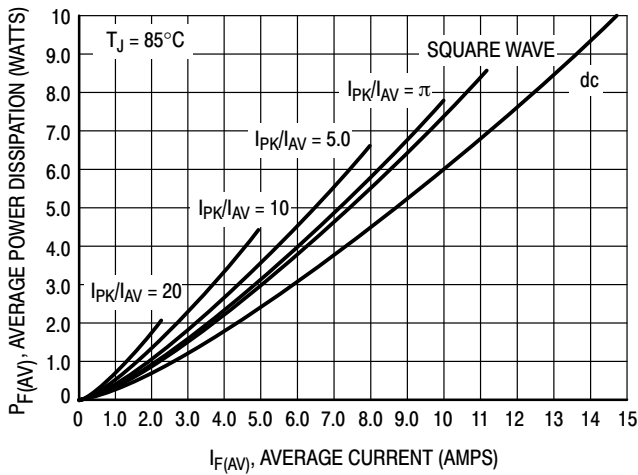
**Figure 2. Typical Reverse Current**



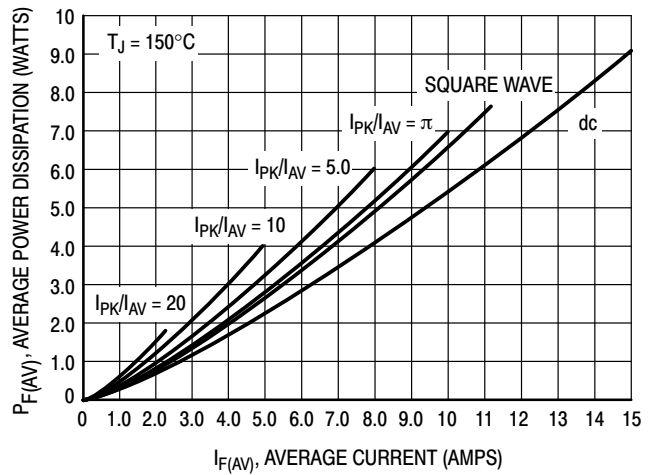
**Figure 3. Current Derating, Case**



**Figure 4. Typical Capacitance**

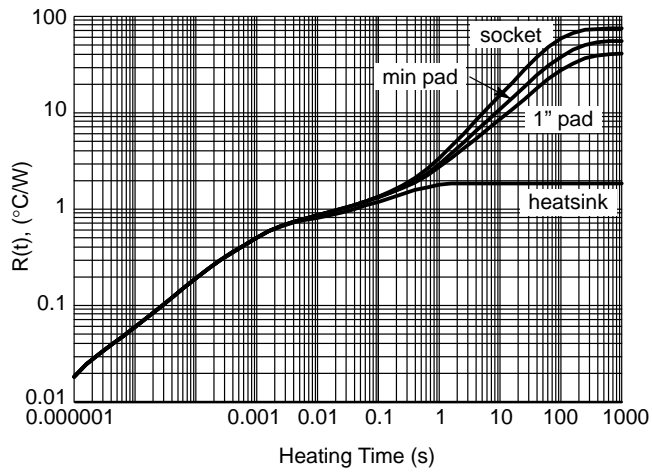


**Figure 5. Typical Forward Power Dissipation**



**Figure 6. Typical Forward Power Dissipation**

# NRVBB1060, NRVBB1060W1

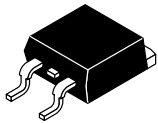


**Figure 7. Single-Pulse Transient Response Curves, Various Mounting Conditions**

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

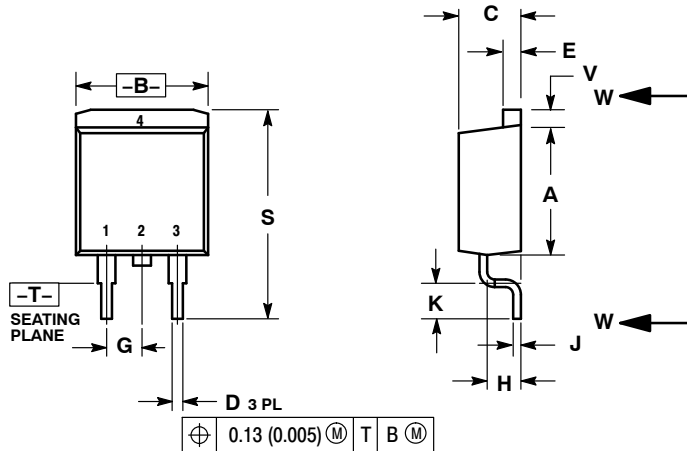
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**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

DATE 17 FEB 2015

SCALE 1:1

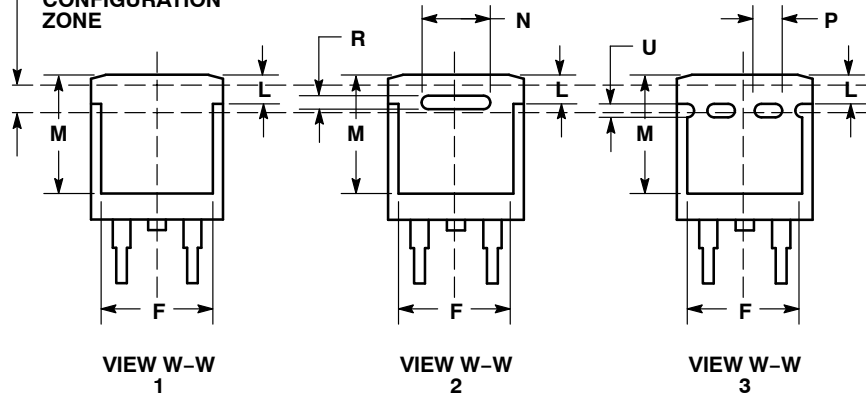


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197	REF	5.00	REF
P	0.079	REF	2.00	REF
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

**VARIABLE CONFIGURATION ZONE**



- |  |   |   |  |   |  |
|--|---|---|--|---|--|
| <b>STYLE 1:</b><br>PIN 1. BASE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | <b>STYLE 2:</b><br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE<br>4. DRAIN | <b>STYLE 3:</b><br>PIN 1. ANODE<br>2. CATHODE<br>3. ANODE<br>4. CATHODE | <b>STYLE 4:</b><br>PIN 1. GATE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | <b>STYLE 5:</b><br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE<br>4. ANODE | <b>STYLE 6:</b><br>PIN 1. NO CONNECT<br>2. CATHODE<br>3. ANODE<br>4. CATHODE |
|--|---|---|--|---|--|

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**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

DATE 17 FEB 2015

**GENERIC  
MARKING DIAGRAM\***



- xx = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package
- AKA = Polarity Indicator

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

**SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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